

# SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

## ABSTRACT OF THE DISCLOSURE

Bit lines having first conductive patterns and bit line mask patterns are formed on a  
5 first insulating layer between capacitor contact regions of a substrate. An oxide second  
insulating layer is formed on the bit lines and contact patterns are formed to open storage  
node contact hole regions corresponding to portions of the second insulating layer. First  
spacers are formed on sidewalls of the etched portions. The second and first insulating layers  
are etched to form storage node contact holes exposing the capacitor contact regions.  
10 Simultaneously, second spacers of the second insulating layer are formed beneath the first  
spacers. A second conductive layer fills the storage node contact holes to form storage node  
contact pads. A loss of the bit line mask pattern decreases due to the reduced thickness of the  
bit line mask pattern and a bit line loading capacitance decreases due to the second spacers.